

MMBT2222ATT1

Preferred Device

General Purpose Transistor

NPN Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-416/SC-75 package which is designed for low power surface mount applications.

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	75	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current - Continuous	I_C	600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation (Note 1) $T_A = 25^\circ\text{C}$	P_D	150	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

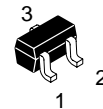
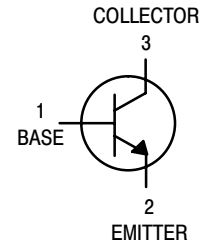
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Device mounted on FR4 glass epoxy printed circuit board using the minimum recommended footprint.



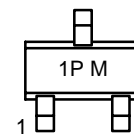
ON Semiconductor®

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CASE 463
SOT-416/SC-75
STYLE 1

MARKING DIAGRAM



1P = Specific Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
MMBT2222ATT1	SOT-416	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ⁽¹⁾ (I _C = 1.0 mAdc, I _B = 0)	V _{(BR)CEO}	40	—	Vdc
Collector–Base Breakdown Voltage (I _C = 10 μAdc, I _E = 0)	V _{(BR)CBO}	75	—	Vdc
Emitter–Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)	V _{(BR)EBO}	6.0	—	Vdc
Base Cutoff Current (V _{CE} = 60 Vdc, V _{EB} = 3.0 Vdc)	I _{BL}	—	20	nAdc
Collector Cutoff Current (V _{CE} = 60 Vdc, V _{EB} = 3.0 Vdc)	I _{CEX}	—	10	nAdc

ON CHARACTERISTICS (Note 2)

DC Current Gain (I _C = 0.1 mAdc, V _{CE} = 10 Vdc) (I _C = 1.0 mAdc, V _{CE} = 10 Vdc) (I _C = 10 mAdc, V _{CE} = 10 Vdc) (I _C = 150 mAdc, V _{CE} = 10 Vdc) (I _C = 500 mAdc, V _{CE} = 10 Vdc)	H _{FE}	35 50 75 100 40	— — — — —	—
Collector–Emitter Saturation Voltage (I _C = 150 mAdc, I _B = 15 mAdc) (I _C = 500 mAdc, I _B = 50 mAdc)	V _{CE(sat)}	— —	0.3 1.0	Vdc
Base–Emitter Saturation Voltage (I _C = 150 mAdc, I _B = 15 mAdc) (I _C = 500 mAdc, I _B = 50 mAdc)	V _{BE(sat)}	0.6 —	1.2 2.0	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product (I _C = 20 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	f _T	300	—	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	—	8.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	—	30	pF
Input Impedance (V _{CE} = 10 Vdc, I _C = 10 mAdc, f = 1.0 kHz)	h _{ie}	0.25	1.25	k ohms
Voltage Feedback Ratio (V _{CE} = 10 Vdc, I _C = 10 mAdc, f = 1.0 kHz)	h _{re}	—	4.0	X 10 ⁻⁴
Small–Signal Current Gain (V _{CE} = 10 Vdc, I _C = 10 mAdc, f = 1.0 kHz)	h _{fe}	75	375	—
Output Admittance (V _{CE} = 10 Vdc, I _C = 10 mAdc, f = 1.0 kHz)	h _{oe}	25	200	μmhos
Noise Figure (V _{CE} = 10 Vdc, I _C = 100 μAdc, R _S = 1.0 k ohms, f = 1.0 kHz)	NF	—	4.0	dB

SWITCHING CHARACTERISTICS

Delay Time	(V _{CC} = 3.0 Vdc, V _{BE} = -0.5 Vdc, I _C = 150 mAdc, I _{B1} = 15 mAdc)	t _d	—	10	ns
Rise Time		t _r	—	25	
Storage Time	(V _{CC} = 30 Vdc, I _C = 150 mAdc, I _{B1} = I _{B2} = 15 mAdc)	t _s	—	225	ns
Fall Time		t _f	—	60	

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

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SWITCHING TIME EQUIVALENT TEST CIRCUITS

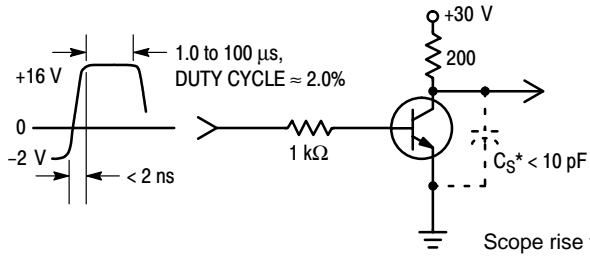


Figure 1. Turn-On Time

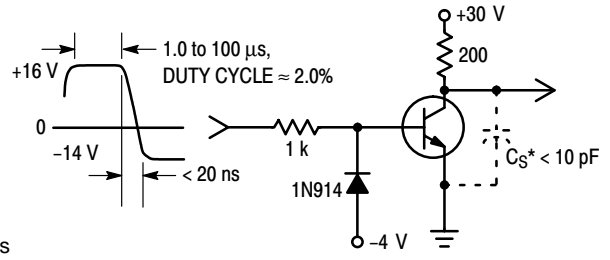


Figure 2. Turn-Off Time

Scope rise time $< 4\text{ ns}$
 *Total shunt capacitance of test jig, connectors, and oscilloscope.

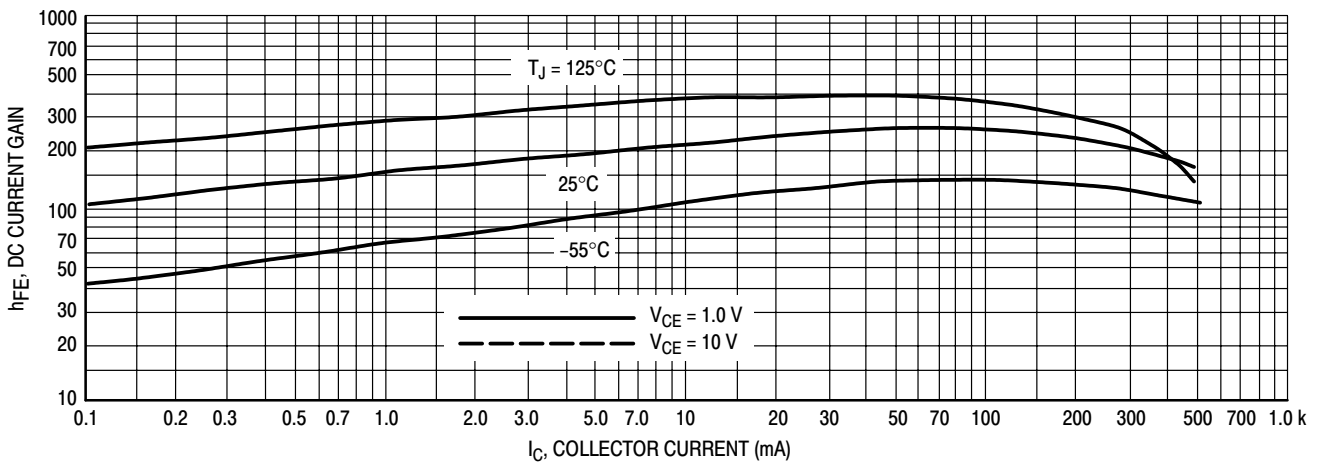


Figure 3. DC Current Gain

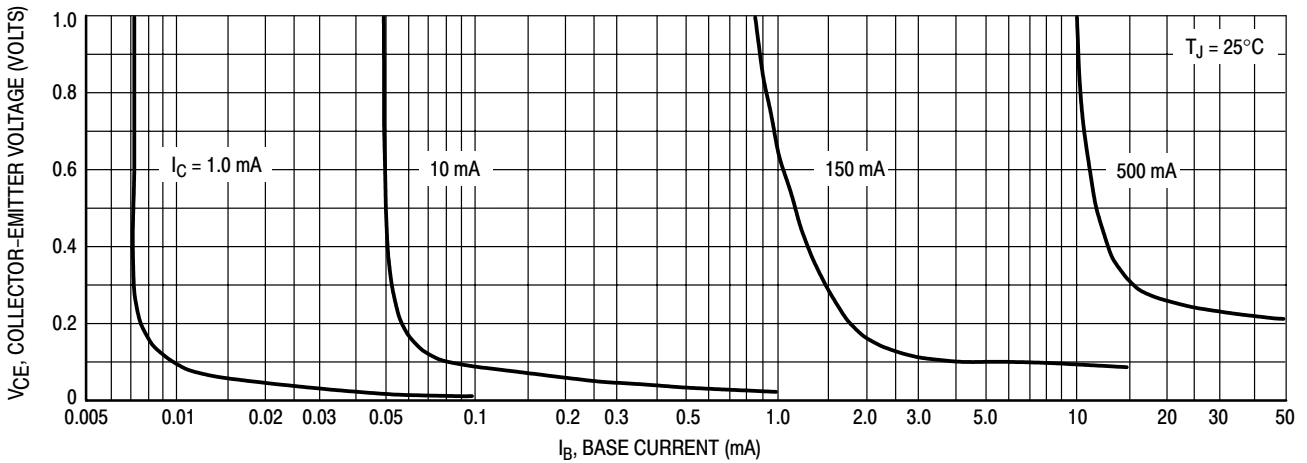


Figure 4. Collector Saturation Region

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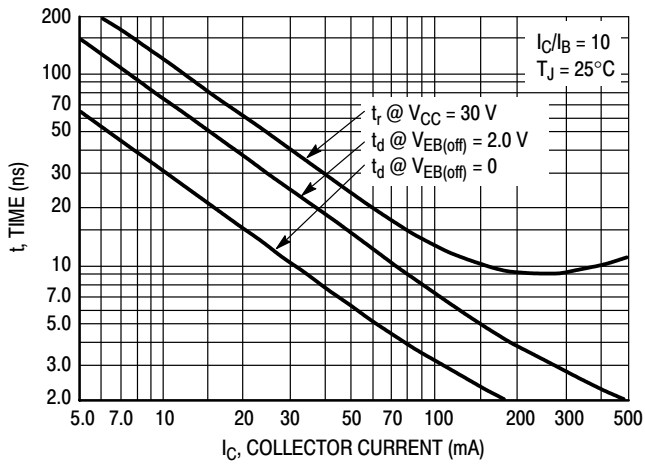


Figure 5. Turn-On Time

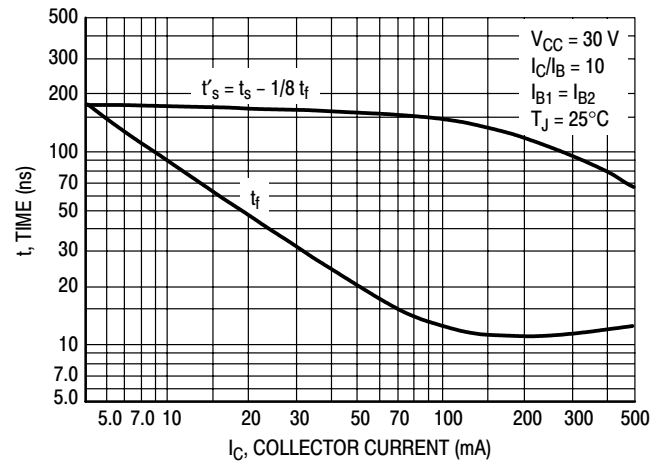


Figure 6. Turn-Off Time

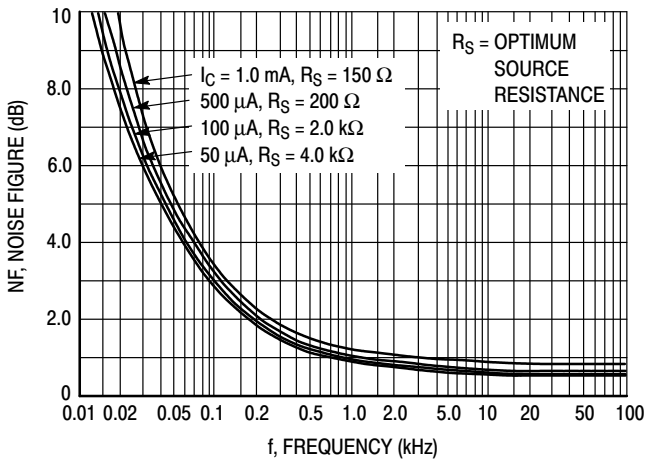


Figure 7. Frequency Effects

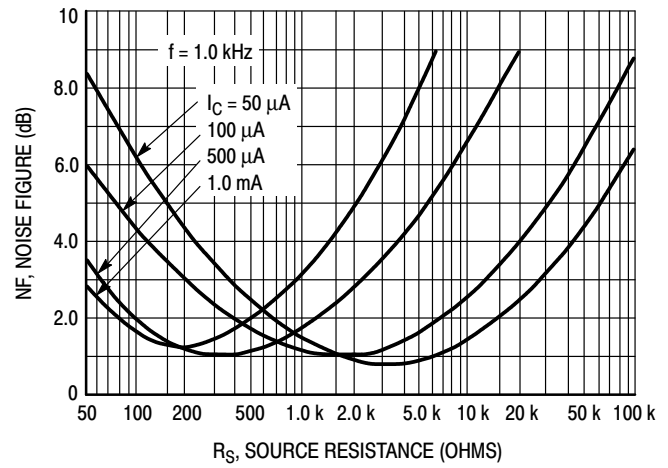


Figure 8. Source Resistance Effects

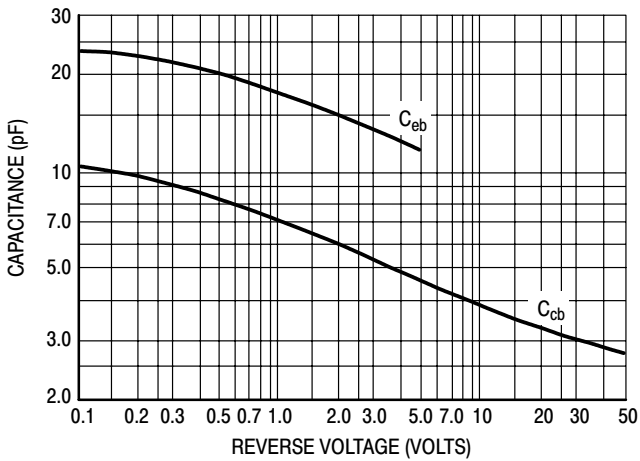


Figure 9. Capacitances

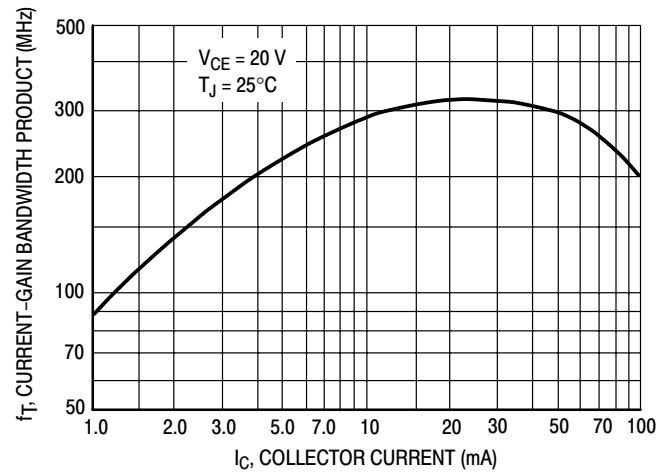


Figure 10. Current-Gain Bandwidth Product

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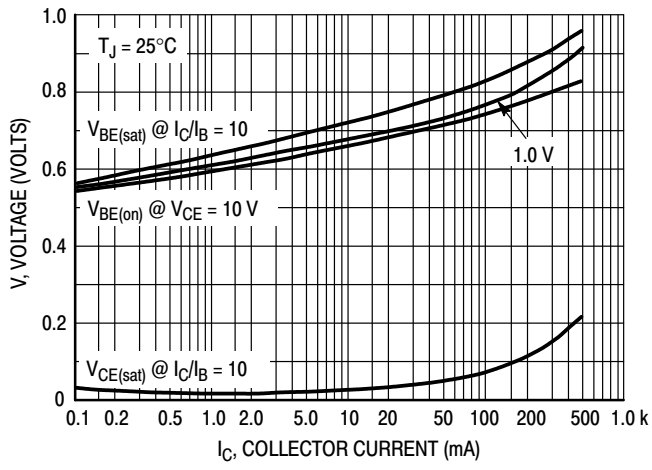


Figure 11. "On" Voltages

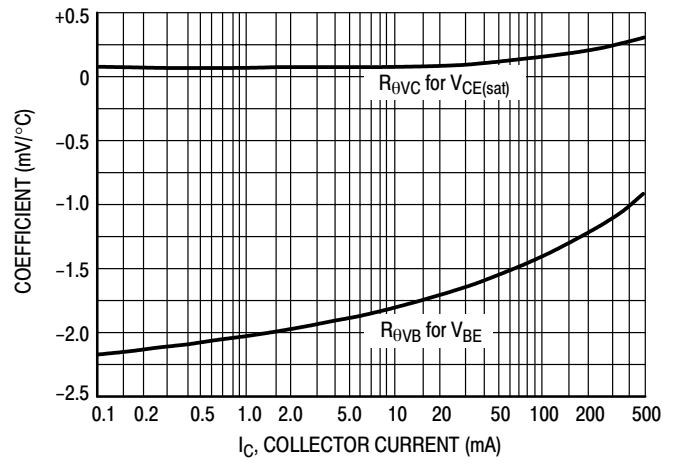
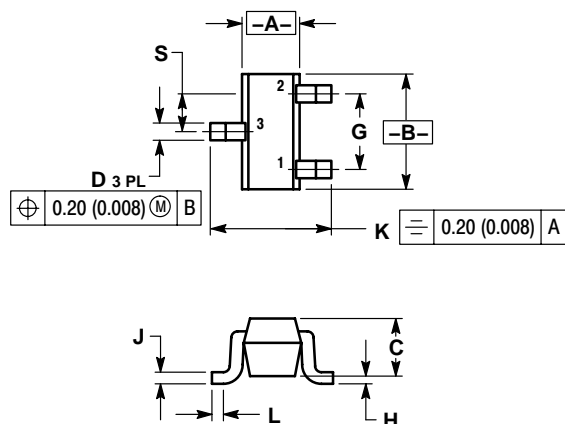


Figure 12. Temperature Coefficients

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PACKAGE DIMENSIONS

SC-75/SOT-416
CASE 463-01
ISSUE C




NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.70	0.90	0.028	0.035
B	1.40	1.80	0.055	0.071
C	0.60	0.90	0.024	0.035
D	0.15	0.30	0.006	0.012
G	1.00 BSC		0.039 BSC	
H	---	0.10	---	0.004
J	0.10	0.25	0.004	0.010
K	1.45	1.75	0.057	0.069
L	0.10	0.20	0.004	0.008
S	0.50 BSC		0.020 BSC	

STYLE 1:

- PIN 1. BASE
2. EMITTER
3. COLLECTOR

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